

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a Q _g (Typ				
30	0.0048 at V _{GS} = 10 V	26	26.5 nC			
	0.006 at V _{GS} = 4.5 V	23.3	20.3 110			

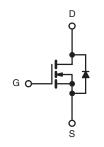
FEATURES

- Halogen-free
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested



APPLICATIONS

- DC/DC Conversion
 - Low-Side Switch
- Notebook PC
- Gaming



N-Channel MOSFET

PowerPAK SO-8
6.15 mm 5.15 mm 2 3 4 G
Bottom View

ABSOLUTE MAXIMUM RATIN	IGS T _A = 25 °C	unless othe	rwise noted		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	± 20	v	
	T _C = 25 °C		26		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	l _D	22.6		
Continuous Brain Gunent (1) = 100 G)	T _A = 25 °C	1 ' ^D	21.5 ^{b, c}		
	T _A = 70 °C	1	17.1 ^{b, c}	Α	
Pulsed Drain Current		I _{DM}	70	A	
Oction Desire District	T _C = 25 °C	I.	5.4		
Continuous Source-Drain Diode Current	T _A = 25 °C	l _S	2.7 ^{b, c}		
Single Pulse Avalanche Current Avalanche Energy L = 0.1 mH		I _{AS}	40		
		E _{AS}	80	mJ	
	T _C = 25 °C		6.0		
Maximum Power Dissipation	T _C = 70 °C		3.3	w	
	T _A = 25 °C	P _D	3.0 ^{b, c}		
	T _A = 70 °C	1 1	1.9 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	33	42	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	16	21	0/11		

- a. Based on T_C = 25 °C.
 b. Surface Mounted on 1" x 1" FR4 board.
- d. Maximum under Steady State conditions is 85 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}$	30			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050A		27		mV/°(
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	- I _D = 250 μA		- 5.6		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.2		2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zara Cata Valtana Brain Correct	1	V _{DS} = 30 V, V _{GS} = 0 V			1	μА
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α
	В	V _{GS} = 10 V, I _D = 15 A		0.0036	0.0048	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$		0.0052	0.0060	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		75		S
Dynamic ^b						
Input Capacitance	C _{iss}			3545		
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		650		pF
Reverse Transfer Capacitance	C _{rss}	1		240		
Tatal Cata Obayera	Q_g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		62	95	nC
Total Gate Charge				26.5	40	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 10 \text{ A}$		8.5		
Gate-Drain Charge	Q _{gd}			7.3		
Gate Resistance	R_g	f = 1 MHz	0.2	1.1	2.2	Ω
Turn-On Delay Time	t _{d(on)}			35	60	ns
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 1.5 \Omega$		16	30	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		48	85	
Fall Time	t _f			16	30	
Turn-On Delay Time	t _{d(on)}			18	35	
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 1.5 \Omega$		8	16	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		41	75	
Fall Time	t _f			8	18	
Drain-Source Body Diode Characteristi	cs					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			5.4	Λ
Pulse Diode Forward Current ^a	I _{SM}				70	A
Body Diode Voltage	V _{SD}	I _S = 3 A		0.72	1.1	V
Body Diode Reverse Recovery Time	t _{rr}			33	65	ns
Body Diode Reverse Recovery Charge	Q _{rr}	1 10 A dl/dt 100 A/: T 05 00		27	54	nC
Reverse Recovery Fall Time	t _a	$I_F = 10 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		17		
Reverse Recovery Rise Time t _b		1		16		ns

Notes:

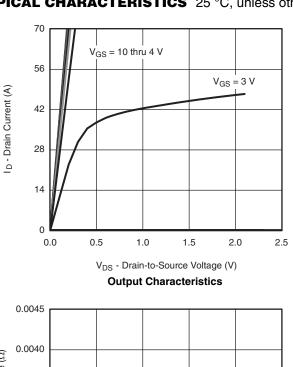
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

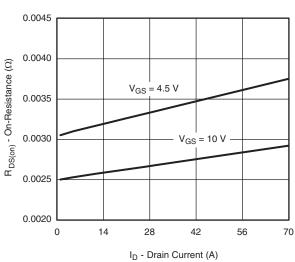
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$

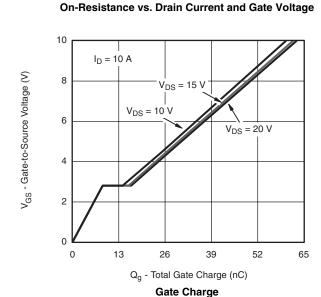
b. Guaranteed by design, not subject to production testing.

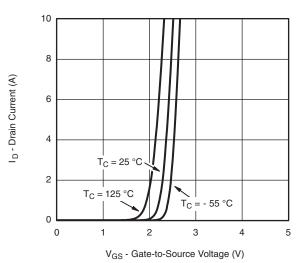


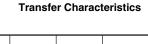
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

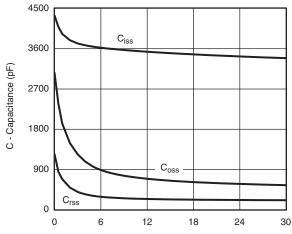




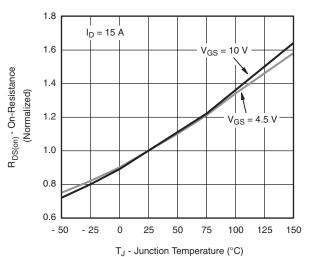








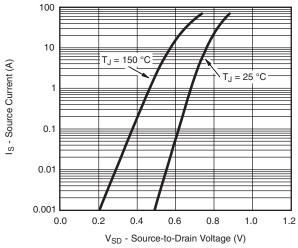
V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



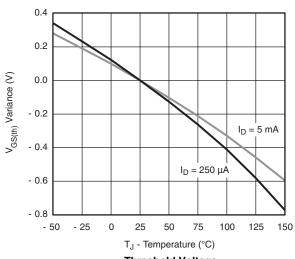
On-Resistance vs. Junction Temperature



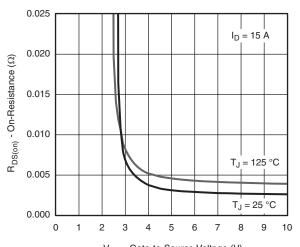
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Source-Drain Diode Forward Voltage

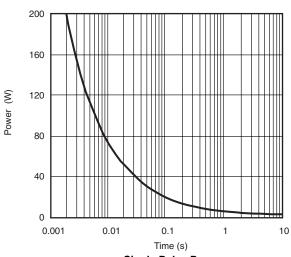


Threshold Voltage

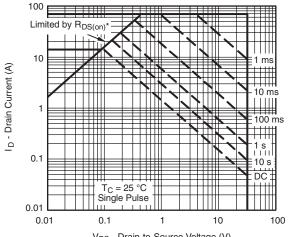


V_{GS} - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power

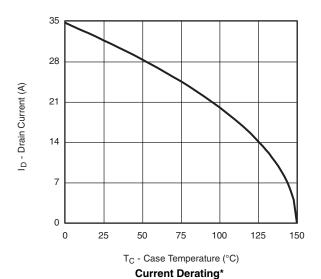


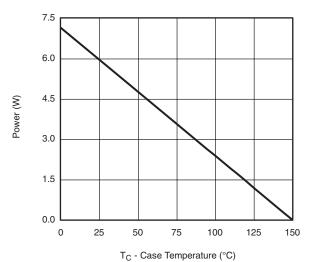
 $V_{DS} \text{ - Drain-to-Source Voltage (V)} \\ ^*V_{GS} > \text{ minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified}$

Safe Operating Area, Junction-to-Ambient

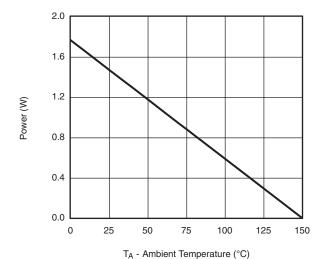


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Power Derating, Junction-to-Foot

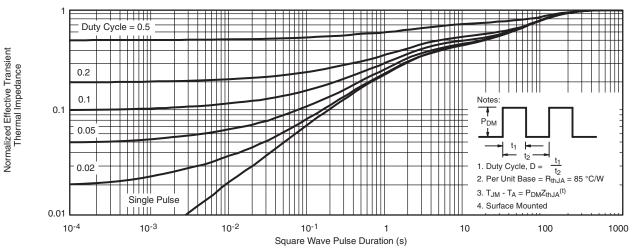


Power, Junction-to-Ambient

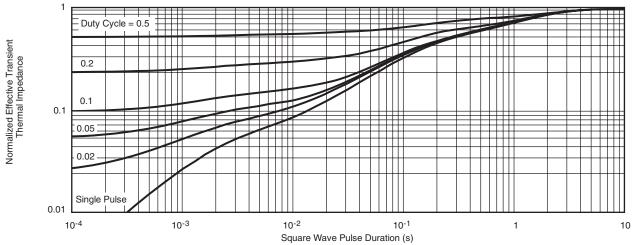
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



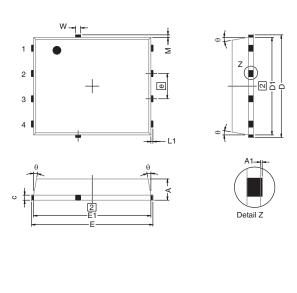
Normalized Thermal Transient Impedance, Junction-to-Ambient

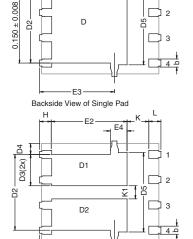


Normalized Thermal Transient Impedance, Junction-to-Foot



PowerPAK SO-8, (SINGLE/DUAL)





Notes

- 1. Inch will govern.
- 2 Dimensions exclusive of mold gate burrs.
- 3. Dimensions exclusive of mold flash and cutting burrs.

-E3 Backside View of Dual Pad

	MILLIMETERS			INCHES				
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Α	0.97	1.04	1.12	0.038	0.041	0.044		
A1	0.00	-	0.05	0.000	-	0.002		
b	0.33	0.41	0.51	0.013	0.016	0.020		
С	0.23	0.28	0.33	0.009	0.011	0.013		
D	5.05	5.15	5.26	0.199	0.203	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.56	3.76	3.91	0.140	0.148	0.154		
D3	1.32	1.50	1.68	0.052	0.059	0.066		
D4		0.57 TYP.		0.0225 TYP.				
D5		3.98 TYP.		0.157 TYP.				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	5.79	5.89	5.99	0.228	0.232	0.236		
E2	3.48	3.66	3.84	0.137	0.144	0.151		
E3	3.68	3.78	3.91	0.145	0.149	0.154		
E4		0.75 TYP.			0.030 TYP.			
е	1.27 BSC			0.050 BSC				
K		1.27 TYP.		0.050 TYP.				
K1	0.56	-	-	0.022	-	-		
Н	0.51	0.61	0.71	0.020	0.024	0.028		
L	0.51	0.61	0.71	0.020	0.024	0.028		
L1	0.06	0.13	0.20	0.002	0.005	0.008		
θ	0°	-	12°	0°	-	12°		
W	0.15	0.25	0.36	0.006	0.010	0.014		
M	0.125 TYP.				0.005 TYP.	•		

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DWG: 5881





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